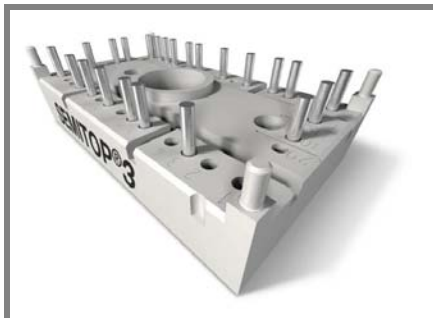


SK75GBB066T



SEMITOP® 3

IGBT Module

SK75GBB066T

Target Data

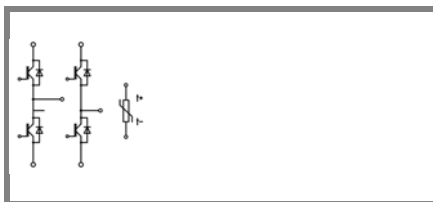
Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Trench IGBT technology
- CAL HD technology FWD
- Integrated NTC temperature sensor

Typical Applications*

Remarks

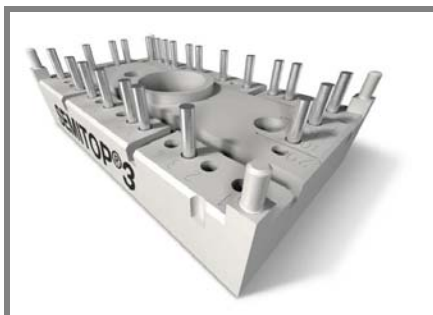
- $V_{isol} = 3000V$ AC, 50Hz, 1s



GBB-T

Absolute Maximum Ratings		$T_s = 25\text{ °C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}	$T_j = 25\text{ °C}$	600	V
I_C	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$	77 A
		$T_s = 70\text{ °C}$	60 A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	150	A
V_{GES}		± 20	V
t_{psc}	$V_{CC} = 360\text{ V}$; $V_{GE} \leq 20\text{ V}$; $T_j = 150\text{ °C}$ $V_{CES} < 600\text{ V}$	6	μs
Inverse Diode			
I_F	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$	77 A
		$T_s = 70\text{ °C}$	60 A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	150	A
I_{FSM}	$t_p = 10\text{ ms}$; half sine wave $T_j = 150\text{ °C}$	395	A
Module			
$I_{t(RMS)}$			A
T_{vj}		-40 ... +175	$^{\circ}\text{C}$
T_{stg}		-40 ... +125	$^{\circ}\text{C}$
V_{isol}	AC, 1 min.	2500	V

Characteristics		$T_s = 25\text{ °C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 1,2\text{ mA}$	5	5,8	6,5	V
I_{CES}	$V_{GE} = 0\text{ V}$, $V_{CE} = V_{CES}$	$T_j = 25\text{ °C}$		0,0038	mA
		$T_j = 125\text{ °C}$			mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = 20\text{ V}$	$T_j = 25\text{ °C}$		600	nA
		$T_j = 125\text{ °C}$			nA
V_{CE0}		$T_j = 25\text{ °C}$	0,8	1,1	V
		$T_j = 150\text{ °C}$	0,7	1	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}$	8	10	$\text{m}\Omega$
		$T_j = 150\text{ °C}$	12,7	14	$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 75\text{ A}$, $V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}_{chiplev.}$	1,45	1,85	V
		$T_j = 150\text{ °C}_{chiplev.}$	1,65	2,05	V
C_{ies}	$V_{CE} = 25$, $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	4,7		nF
C_{oes}			0,3		nF
C_{res}			0,145		nF
Q_G	$V_{GE} = -7V...+15V$		700		nC
$t_{d(on)}$	$R_{Gon} = 16\ \Omega$ $di/dt = 2250\text{ A}/\mu\text{s}$	$V_{CC} = 300V$ $I_C = 75A$	95		ns
t_r			50		ns
E_{on}			3,1		mJ
$t_{d(off)}$	$R_{Goff} = 16\ \Omega$ $di/dt = 2250\text{ A}/\mu\text{s}$	$T_j = 150\text{ °C}$ $V_{GE} = -7/+15\text{ V}$	541		ns
t_f			70		ns
E_{off}			2,8		mJ
$R_{th(j-s)}$	per IGBT		0,94		K/W



SEMITOP[®] 3

IGBT Module

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Target Data

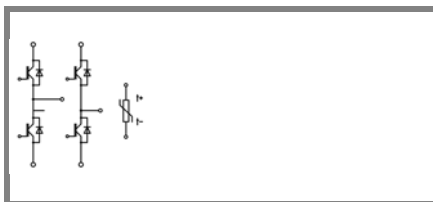
Features

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Typical Applications*

Remarks

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GBB-T

Characteristics

Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 75 A; V_{GE} = 0 V$				
	$T_j = 25 ^\circ C_{chiplev.}$		1,35		V
	$T_j = 150 ^\circ C_{chiplev.}$		1,31		V
V_{F0}					V
	$T_j = 25 ^\circ C$				V
	$T_j = 150 ^\circ C$		0,85		V
r_F					mΩ
	$T_j = 25 ^\circ C$				mΩ
	$T_j = 150 ^\circ C$		7,8		mΩ
I_{RRM}	$I_F = 75 A$		60		A
Q_{rr}	$di/dt = 2250 A/\mu s$		6		μC
E_{rr}	$V_{CC} = 300V$		0,85		mJ
$R_{th(j-s)D}$	per diode		1,55		K/W
M_s	to heat sink	2,5		2,75	Nm
w			60		g
Temperature sensor					
R_{100}	$T_s = 100^\circ C (R_{25} = 5k\Omega)$		493±5%		Ω

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

